

**Please amend claims 1, 3-6, 22, 26, 28-31, 35 and 37 as follows:**

1. (Amended) A process for fabricating a thin-film device, said process comprising:

forming a conducting layer composed of an anodically oxidizable metal on a substrate;

etching said conducting layer to form a plurality of bus lines having upper surfaces parallel to said substrate and inclined side surfaces and connection portions electrically connected to said bus lines and having upper surfaces parallel to said substrate and inclined side surfaces, the side surfaces of said bus lines and the side surfaces of said conduction portion are outwardly convex;

anodically oxidizing said bus lines and said connection portions so that said bus lines and said connection portions include inner conducting portions and outer insulating oxide films covering said inner conducting portions, respectively.

3. (Amended) A process according to claim 2, wherein said etching is carried out so that the side surfaces of said bus lines and the side surfaces of said connection portions are inclined at angles within the range from 30 degrees to 50 degrees, an average, with respect to said substrate.

4. (Amended) A process according to claim 1, further comprising forming a mask on said conducting layer prior to said etching, and ashing said substrate including said mask between said mask forming and said etching.

B<sup>2</sup> 5. (Amended) A process according to claim 1, further comprising forming a mask on said conducting layer and baking said mask prior to said etching, wherein the temperature for baking said mask is so set that said mask will have a relatively small rigidity so that an outer portion of said mask is pushed up from said conducting layer due to a reaction gas in said etching.

6. (Amended) A process according to claim 5, wherein the temperature for baking said mask is not higher than 115°C.

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22. (Amended) A process for fabricating a thin-film device, said process comprising:  
forming a conducting layer composed of an anodically oxidizable metal on  
a substrate;  
B<sup>3</sup> etching said conducting layer in a predetermined shape;  
forming a second oxide film on said conducting layer by anodic oxidation  
after a first oxide film with a thickness is formed on said conducting layer; and  
washing said substrate, whereby said first oxide film is removed by said  
washing and said second oxide film is not removed by said washing but remains on said conducting  
layer so as to cover said conducting layer.

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B<sup>4</sup> 26. (Amended) A process according to claim 22, wherein said washing is executed using  
ultrasonic waves of not lower than 200 KHz.

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28. (Amended) A process according to claim 27, further comprising forming an insulating film on said substrate and forming a semiconductor layer on said substrate after the second oxide film has been formed, wherein the etching of said conducting layer forms gate electrodes and gate wirings.

29. (Amended) A process according to claim 27, further comprising forming a semiconductor layer on said substrate and forming an insulating film on said substrate prior to forming said conducting layer, wherein the of said conducting layer forms gate electrodes and gate wirings.

30. (Amended) A process according to claim 22, wherein the etching of said conducting layer forms gate electrodes having upper surfaces parallel to said substrate and inclined side surfaces.

31. (Amended) A process for fabricating a thin-film device, said process comprising:

- forming a semiconductor layer having a predetermined shape on a substrate;
- forming an insulating film on said substrate to cover said semiconductor layer;
- forming a conducting layer composed of an anodically oxidizable metal on said substrate in such a shape as to cover a portion of said semiconductor layer and to form gate electrodes having upper surfaces parallel to said substrate and inclined side surfaces;
- anodically oxidizing said gate electrodes;

forming said insulating film into a predetermined shape using said gate electrodes including the anodically oxidized film as a mask; and

injecting impurities into said semiconductor layer using said gate electrodes including said anodically oxidized film and said insulating film as a mask to form an offset in said semiconductor layer.

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35. (Amended) A process according to claim 31, wherein said semiconductor layer comprises a polycrystalline silicon.

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37. (Amended) A process according to claim 31, wherein forming said gate electrodes comprises forming a gate electrode layer and patterning the gate electrode layer based on either ionic milling or dry-etching.

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